

General Description

The WST3013 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The WST3013 meet the RoHS and Green Product requirement, with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

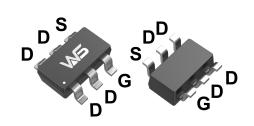
Product Summery

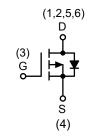
BV _{DSS}	R _{DSON}	I _D
-12V	38mΩ	-4.4A

Applications

- Portable Equipment and Battery Powered Systems.
- Power Management in Notebook
 Computer

SOT-23-6L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-12	V
V_{GS}	Gate-Source Voltage	±8	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ -4.5V ¹	-4.4	Α
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-3.5	Α
I _{DM}	Pulsed Drain Current ²	-17.7	Α
P _D @T _A =25℃	Total Power Dissipation ³	2.1	W
T _{STG}	Storage Temperature Range	-55 to 150	${\mathbb C}$
T_J	Operating Junction Temperature Range -55 to 150		

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-Ambient ¹		100	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		80	°C/W





Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-12			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.014		V/°C	
В	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V , I _D =-4.4A		38	60	mO	
R _{DS(ON)}	Static Dialii-Source Off-Resistance	V _{GS} =-2.5V , I _D =-3.5A 47		47	90	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} . In =-250uA	-0.5	-0.7	-1.0	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} -V _{DS} , I _D 250uA		3.95		mV/℃	
l	Drain-Source Leakage Current	V_{DS} =-8V , V_{GS} =0V , T_J =25 $^{\circ}\mathrm{C}$			-1	uA	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-8V , V_{GS} =0V , T_J =55 $^{\circ}\mathrm{C}$			-5	uA	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 8V$, V_{DS} = $0V$			±100	nA	
gfs	Forward Transconductance	V_{DS} =-5V , I_{D} =-3A		8		8	
Q_g	Total Gate Charge (-4.5V)			5.2			
Q_{gs}	Gate-Source Charge	V _{DS} =-10V , V _{GS} =-4.5V , I _D =-4.4A		0.7		nC	
Q_gd	Gate-Drain Charge			1.8			
$T_{d(on)}$	Turn-On Delay Time			5.6			
T _r	Rise Time	V _{DD} =-10V , V _{GEN} =-4.5V ,		13.2		ns	
$T_{d(off)}$	Turn-Off Delay Time	$R_G=6\Omega$, $I_D=-1A$, $R_L=10\Omega$.		4.5		115	
T _f	Fall Time			21			
C _{iss}	Input Capacitance			357			
Coss	Output Capacitance	V _{DS} =-10V , V _{GS} =0V , f=1MHz		72		pF	
C _{rss}	Reverse Transfer Capacitance			61			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V =V =0V Force Current			-1	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			-17.7	Α
V_{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =-1A , T_{J} =25 $^{\circ}$ C			-1	V
t _{rr}	Reverse Recovery Time			12		nS
Q _{rr}	Reverse Recovery Charge	lF=-4.4A,dl/dt=100A/μs , T _J =25℃		6.6		nC

Note

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3.The power dissipation is limited by 150 ℃ junction temperature
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

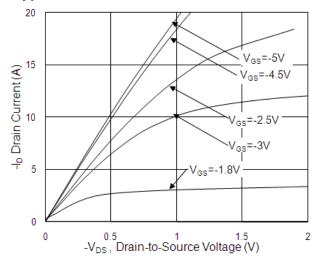


Fig.1 Typical Output Characteristics

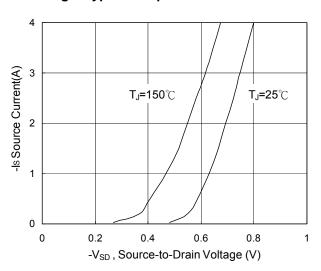


Fig.3 Forward Characteristics of Reverse

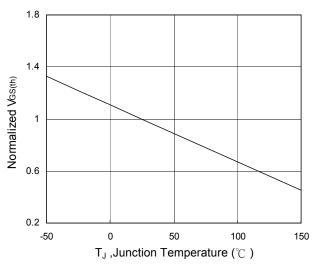


Fig.5 Normalized V_{GS(th)} vs. T_J

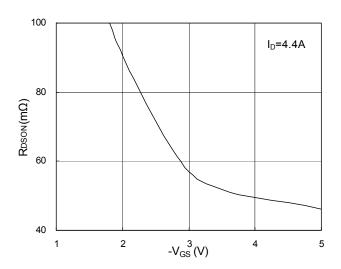


Fig.2 On-Resistance vs. G-S Voltage

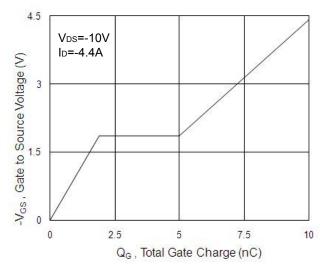


Fig.4 Gate-charge Characteristics

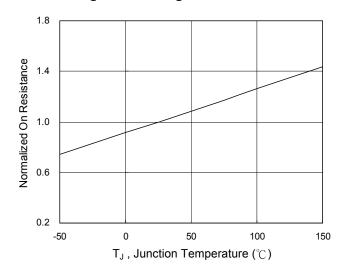
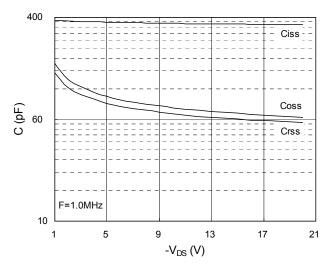


Fig.6 Normalized R_{DSON} vs. T_J





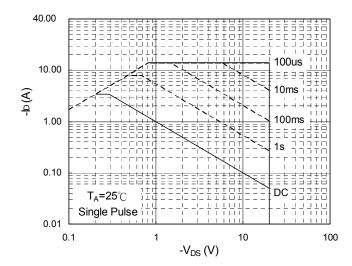


Fig.7 Capacitance

Fig.8 Safe Operating Area

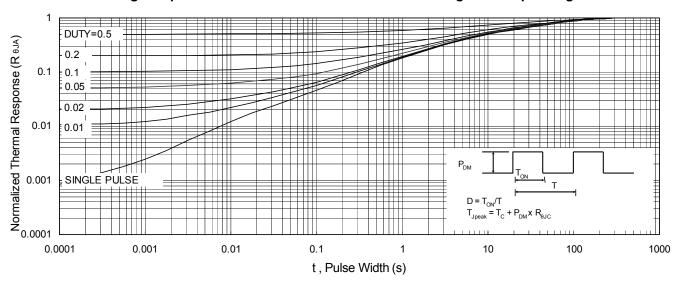
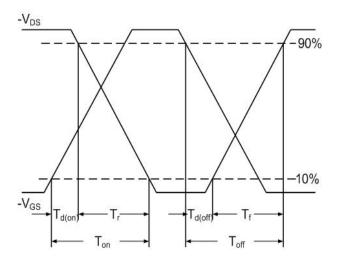


Fig.9 Normalized Maximum Transient Thermal Impedance



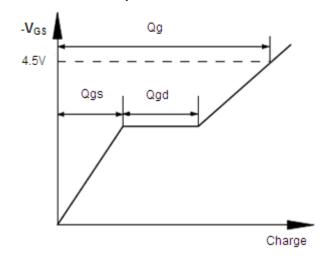
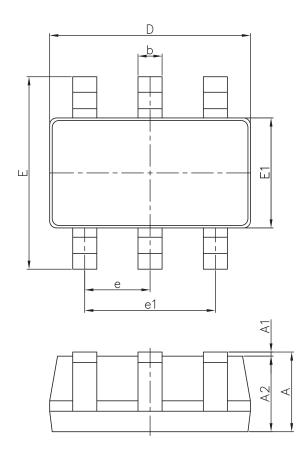


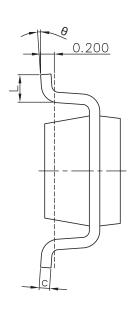
Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform



Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches	
Зуньог	Min.	Max.	Min.	Max.
А	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)	0.037((BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



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